

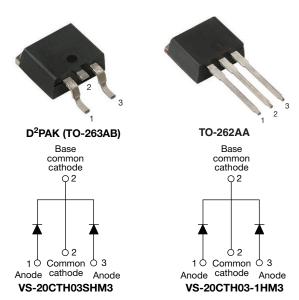
www.vishay.com

Vishay Semiconductors

HALOGEN

FREE

Hyperfast Rectifier, 2 x 10 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)}	2 x 10 A					
V _R	300 V					
V _F at I _F	0.85 V					
t _{rr} typ.	23 ns					
T _J max.	175 °C					
Package	D ² PAK (TO-263AB), TO-262AA					
Circuit configuration	Common cathode					

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201, class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Terminal: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V_{RRM}		300	V			
Average rectified forward current	per diode	1	T _C = 160 °C	10				
Average rectilled forward current	per device	I _{F(AV)}		20	А			
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120				
Operating junction and storage ten	nperatures	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	300	-	-	V			
Farmer of well-are	VF	I _F = 10 A	-	1.05	1.25	V			
Forward voltage	٧F	I _F = 10 A, T _J = 125 °C	ı	0.85	0.95				
Reverse leakage current	I_	$V_R = V_R$ rated	ı	-	20	μA			
Reverse leakage current I _R		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	ı	6	200	μΑ			
Junction capacitance	C _T	$V_{R} = 300 \text{ V}$	-	30	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nΗ			

VS-20CTH03SHM3, VS-20CTH03-1HM3

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 A, dI_F/dt =$	$100 \text{ A/}\mu\text{s}, V_{\text{R}} = 30 \text{ V}$	ı	23	-		
Reverse recovery time	t _{rr}	$T_J = 25 ^{\circ}C$	I _F = 10 A dI _F /dt = 200 A/µs V _B = 200 V	ı	31	-	ns	
		T _J = 125 °C		-	42	-		
Dook recovery current	I _{RRM}	T _J = 25 °C		-	2.4	-	A	
Peak recovery current		T _J = 125 °C		-	5.6	-		
Reverse recovery charge	0	T _J = 25 °C	N - 200 V	-	36	-	nC	
	Q_{rr}	T _J = 125 °C		-	120	-	IIC	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Thermal resistance, junction to case per diode	R _{thJC}		-	-	1.5	°C/W			
Thermal resistance, junction to ambient	R _{thJA}		-	-	70	°C/W			
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Marking davise		Case style D ² PAK (TO-263AB)	20CTH03SH						
Marking device		Case style TO-262AA		20CTH	103-1H				

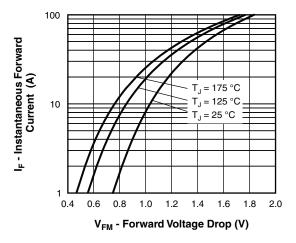


Fig. 1 - Maximum Forward Voltage Drop Characteristics

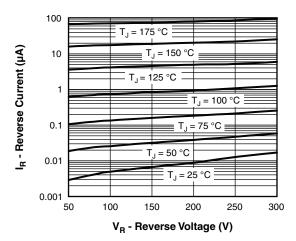


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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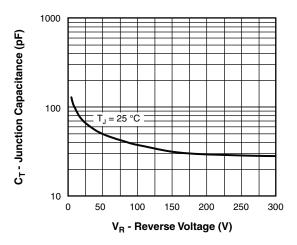


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

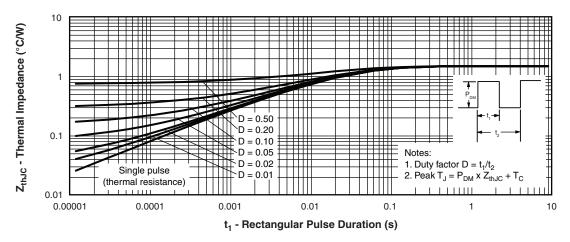


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

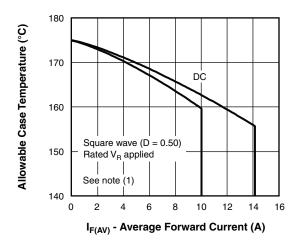


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

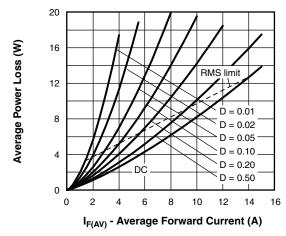


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = rated V_R$

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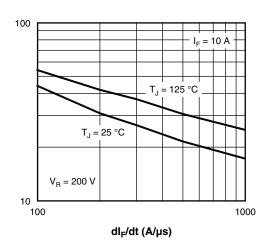


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

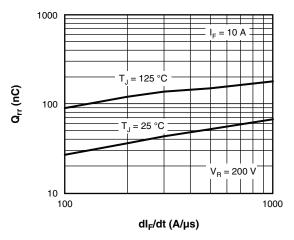
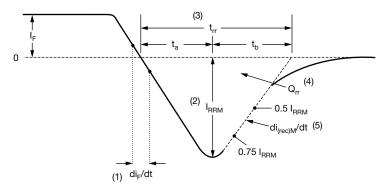


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_{r} to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

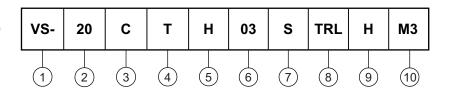
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-20CTH03SHM3, VS-20CTH03-1HM3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (20 A)

C = common cathode

4 - $T = TO-220, D^2PAK$

5 - H = hyperfast rectifier

Voltage rating (03 = 300 V)

7 - • S = D²PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - H = AEC-Q101 qualified

- M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-20CTH03SHM3	50	Antistatic plastic tubes					
VS-20CTH03STRLHM3	800	13" diameter plastic tape and reel					
VS-20CTH03STRRHM3	800	13" diameter plastic tape and reel					
VS-20CTH03-1HM3	50	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS						
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?95046				
	TO-262AA	www.vishay.com/doc?95419				
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444				
	TO-262AA	www.vishay.com/doc?95443				
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?95032				
SPICE model	•	www.vishay.com/doc?96583				



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES SYMBOL MILLIMETERS INCHES		MILLIMETERS		HES	NOTES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

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TO-262

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	METERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.36	3.71	0.132	0.146	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- 5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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